

GaAs MMIC 6-bit digitally controlled phase shifter chip , 0.9-1.3GHz

Performance characteristics

- Frequency range: 0.9 - 1.3 GHz
- Insertion loss: 4.7dB (Typ.)
- Insertion loss fluctuation : 1.1dB
- Phase shift accuracy (RMS): 1.3 °
- 50Ohm input / output
- 100% on-wafer testing
- Chip size 3.95 x 1.57 x 0.1mm

Product Introduction

GPS-009013-6C is a GaAs MMIC 6-bit digitally controlled phase shifter chip with a frequency range of 0.9 GHz ~1.3 GHz , an insertion loss of 4.7 dB , and a phase shift accuracy of 1.3 ° . The chip uses 0/-5V logic control. The chip uses on-chip through-hole metallization technology to ensure good grounding, no additional grounding measures are required, and it is simple and convenient to use. The back of the chip is metallized and is suitable for eutectic sintering or conductive adhesive bonding processes.

Use restriction parameter ¹	
Maximum input power	+25dBm
Control voltage range	-8V ~ +0.5V
Operating temperature	-55 ~ +85°C
Storage temperature	-65 ~ +150°C

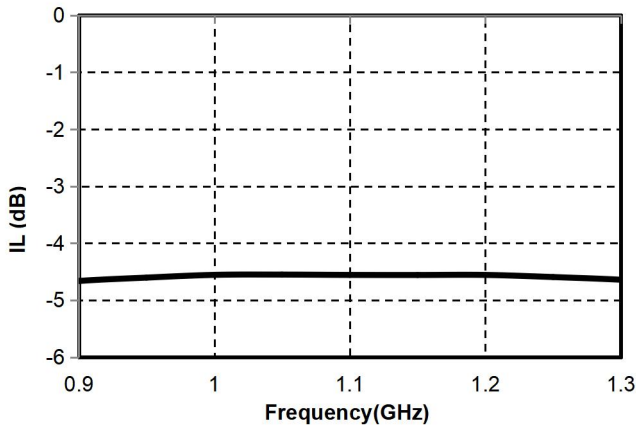
【1】 Exceeding any of these maximum limits may cause permanent damage.

Electrical performance parameters (TA = +25°C)				
Index	Minimum	Typical Value	Maximum	Unit
Frequency Range	0.9-1.3			GHz
Insertion loss	-	4.7	-	dB
Insertion loss fluctuation		1.1		dB
Phase shift accuracy (RMS)		1.3		degree
Input return loss	-	22	-	dB
Output return loss	-	23	-	dB
Switching time		20		ns
P-1		21		dBm

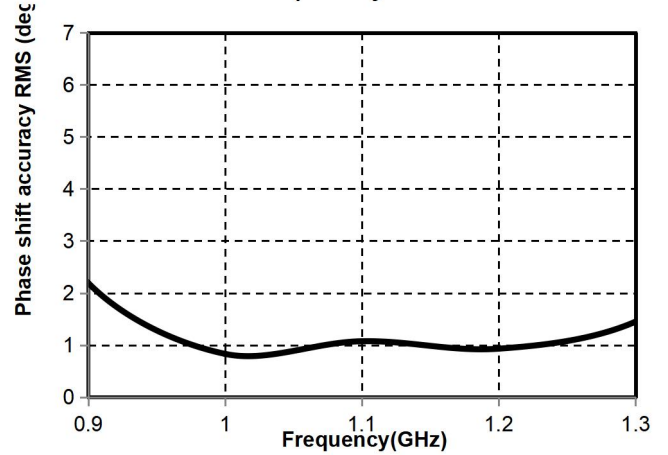
GaAs MMIC 6-bit Digitally Controlled Phase Shifter Chip , 0.9-1.3GHz

Main index test curve

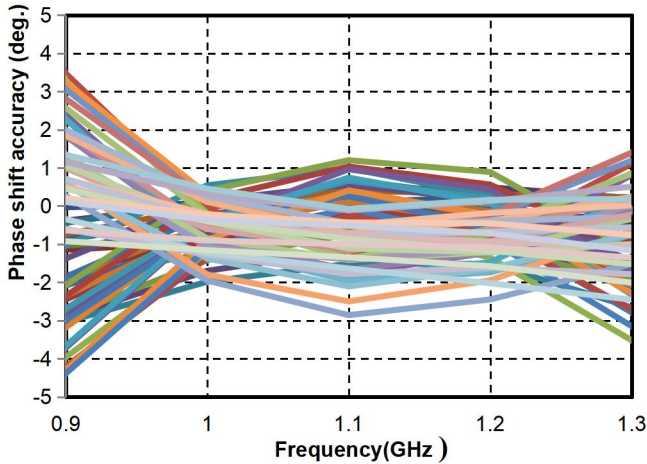
Insertion Loss vs. Operating Frequency



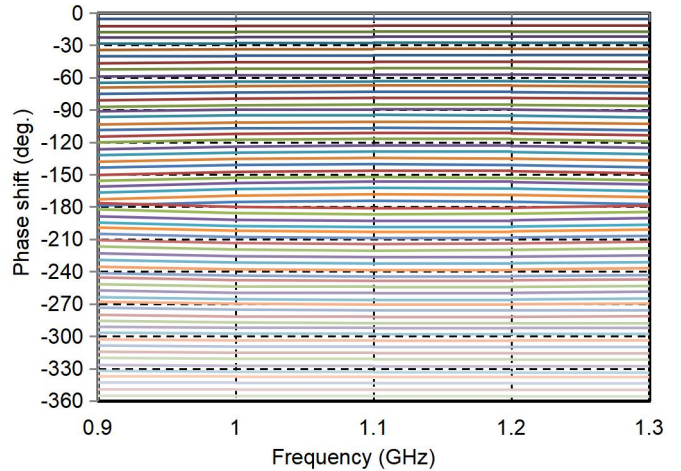
Phase shift accuracy (RMS) vs. operating frequency



Phase shift accuracy (absolute value) vs. operating frequency

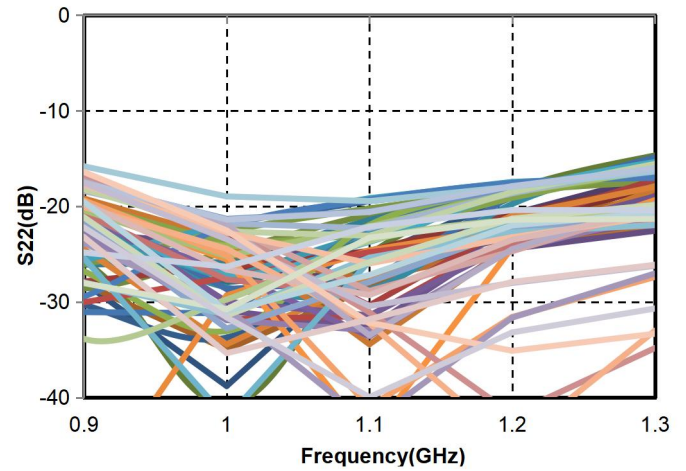
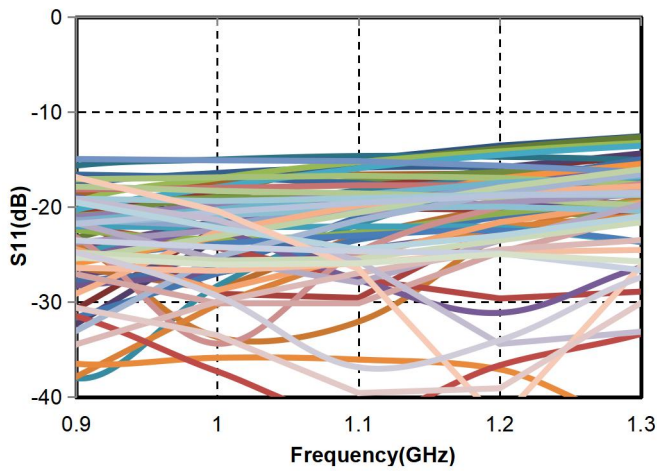


Phase shift vs. operating frequency

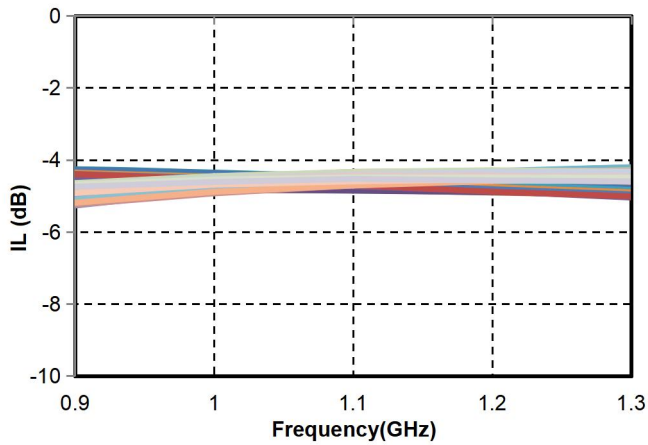


Full-state phase shift input return loss vs. operating frequency

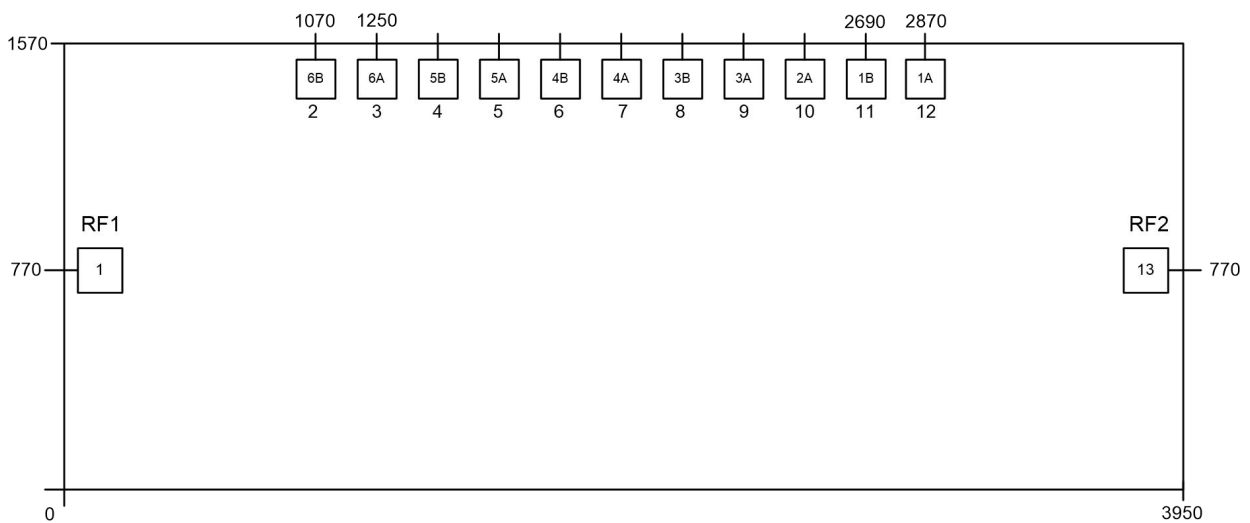
Full-state phase shift output return loss vs. operating frequency



Full-state phase shift insertion loss vs. operating frequency



Appearance structure ²



【 2 】 All units in the figure are micrometers

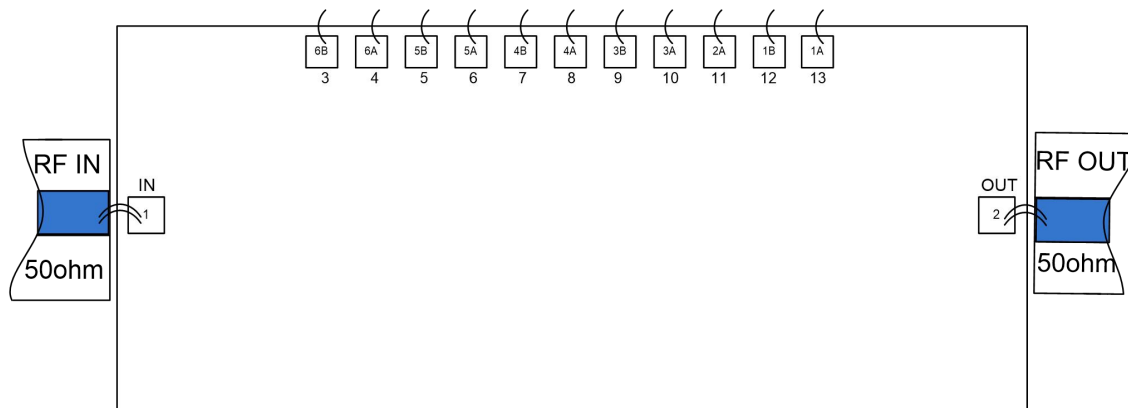
Bonding point definition

Bonding point number	Function Symbol	Functional Description
1	RF IN	RF signal input terminal
13	RF OUT	RF signal output terminal
2~12	CTRL	Control Port
Chip bottom	GND	The bottom of the chip needs to be well grounded to RF and DC

Truth Table

	6B	6A	5B	5A	4B	4A	3B	3A	2A	1B	1A
Ground state	-5	0	0	-5	0	-5	0	-5	-5	0	-5
-5.265°	-5	0	0	-5	0	-5	0	-5	-5	-5	0
-11.25°	-5	0	0	-5	0	-5	0	-5	0	0	-5
-22.5°	-5	0	0	-5	0	-5	-5	0	-5	0	-5
-45°	-5	0	0	-5	-5	0	0	-5	-5	0	-5
-90°	-5	0	-5	0	0	-5	0	-5	-5	0	-5
-180°	0	-5	0	-5	0	-5	0	-5	-5	0	-5

Recommended assembly drawing



Precautions for use

- The chip needs to be stored in an anti-static container and kept in a nitrogen environment.
- bare die surface using wet chemical methods .
- Please strictly follow the ESD protection requirements to avoid static damage to the bare chip.
- General operation: Please use precision pointed tweezers to pick up bare chips. Avoid touching the chip surface with tools or fingers during operation.
- Rack mounting operation suggestions: Bare chip mounting can be done by AuSn solder eutectic sintering or conductive adhesive bonding. The mounting surface must be clean and flat.
- Sintering process: It is recommended to use AuSn solder sheets with a gold -tin ratio of 80/20 . The

working surface temperature reaches 255 °C and the tool (vacuum chuck) temperature reaches 265 °C . When the high-temperature mixed gas (nitrogen-hydrogen ratio of 90/10) is blown to the chip, the temperature at the top of the tool should be raised to 290 °C . Do not let the chip exceed 320 °C for more than 20 seconds. The friction time should not exceed 3 seconds.

- Bonding process: The amount of conductive glue dispensed should be as small as possible. After the chip is placed in the installation position , the conductive glue should be vaguely visible around it . For curing conditions, please follow the information provided by the conductive glue manufacturer.
- Bonding operation suggestions: Use $\Phi 0.025\text{mm}$ (1mil) gold wire for both ball and wedge bonding . Thermo-ultrasonic bonding temperature is 150 °C. The pressure of the wedge for ball bonding is 40~50gf , and the pressure of the wedge bonding is 18~22gf . Use the smallest possible ultrasonic energy. The bonding starts at the pressure point on the chip and ends at the package (or substrate) .